SN74LV1T00 单电源 2 输入正与非门 CMOS 逻辑电平转换器

1 特性

- 5.0/3.3/2.5/1.8V V_{CC} 单电源电压转换器
- 1.8V 至 5.5V 的工作电压范围
  - 上行转换：
    - 1.2V[1] 至 1.8V
    - 1.5V[1] 至 2.5V
    - 1.8V[1] 至 3.3V
    - 3.3V[1] 至 5.0V
  - 下行转换：
    - 5.0V、3.3V、2.5V 至 1.8V
    - 5.0V、3.3V 至 2.5V
    - 5.0 V 至 3.3 V
- 逻辑输出以 V_{CC} 为基准
- 输出驱动
  - 5V 时，8mA 的输出驱动
  - 3.3V 时，7mA 的输出驱动
  - 1.8V 时，3mA 的输出驱动
- 3.3V V_{CC} 时，频率高达 50MHz
- 输入引脚可耐受 5V 电压
- -40°C 至 125°C 工作温度范围
- 可提供无铅封装：SC-70 (DCK)
  - 2mm x 2.1mm x 0.65mm
- 闩锁性能超过 250mA 订单编号封装体尺寸，符合 JESD 17 规范的要求
- 支持标准逻辑引脚排列
- 与 AUP1G 和 LVC1G 系列兼容的 CMOS 输出 B

1. 请参考更低 V_{CC} 条件下的 V_{IH}/V_{IL} 和输出驱动。

2 应用

- 工业用控制器
- 电信
- 便携式应用
- 服务器
- 台式机和笔记本电脑
- 汽车

3 说明

SN74LV1T00 是一款具有较宽电压范围的低压 CMOS 门逻辑电路，用于工业、便携、电信和汽车应用。输出电平以电源电压为基准，能够支持 1.8V/2.5V/3.3V/5V CMOS 电平

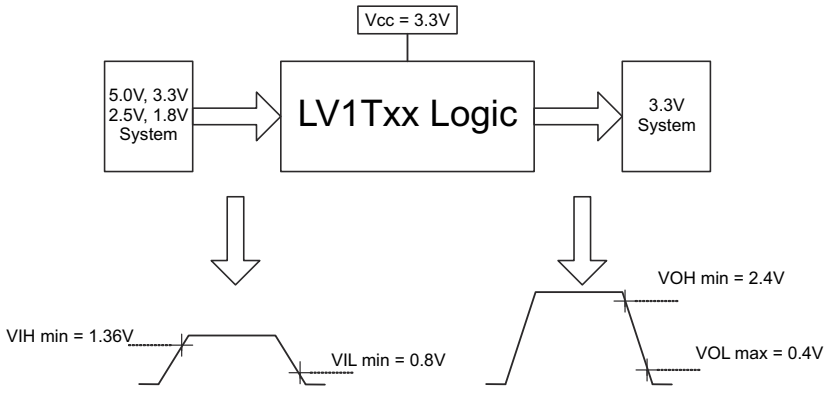
输入采用较低阈值电路设计，以匹配 VCC = 3.3V 时的 1.8V 输入逻辑，并可用于 1.8V 至 3.3V 电平升压转换。此外，5V 容限输入引脚可实现向下转换（例如，在 VCC = 2.5V 时输出 3.3V 至 2.5V）。1.8V 至 5.5V 的宽 VCC 范围使生成的所需输出电平能够连接至控制器或处理器。

SN74LV1T00 被设计成具有 8mA 的电流驱动能力，以减少由高驱动输出导致的线路反射、过冲和下冲。

器件信息

器件型号(1)	封装	封装尺寸（标称值）
SN74LV1T00	DBV（SOT-23，5）	2.90mm × 1.60mm
	DCK（SC70，5）	2.00mm × 1.25mm

(1) 如需了解所有可用封装，请参阅数据表末尾的可订购产品附录。



1.8V 至 3.3V 转换的开关阈值

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4 Revision History

注：以前版本的页码可能与当前版本的页码不同

Changes from Revision B (February 2014) to Revision C (June 2022)	Page
• 更新了整个文档中的表格、图和交叉参考的编号格式	1
• Added Thermal Information table	6
• Added Typical Characteristics	7

5 Related Products

DEVICE	PACKAGE	DESCRIPTION
SN74LV1T00	DCK, DBV	2-Input Positive-NAND Gate
SN74LV1T02	DCK, DBV	2-Input Positive-NOR Gate
SN74LV1T04	DCK, DBV	Inverter Gate
SN74LV1T08	DCK, DBV	2-Input Positive-AND Gate
SN74LV1T17	DCK, DBV	Single Schmitt-Trigger Buffer Gate
SN74LV1T14	DCK, DBV	Single Schmitt-Trigger Inverter Gate
SN74LV1T32	DCK, DBV	2-Input Positive-OR Gate
SN74LV1T34	DCK, DBV	Single Buffer Gate
SN74LV1T86	DCK, DBV	Single 2-Input Exclusive-Or Gate
SN74LV1T125	DCK, DBV	Single Buffer Gate with 3-state Output
SN74LV1T126	DCK, DBV	Single Buffer Gate with 3-state Output
SN74LV4T125	RGY, PW	Quadruple Bus Buffer Gate With 3-State Outputs

6 Pin Configuration and Functions

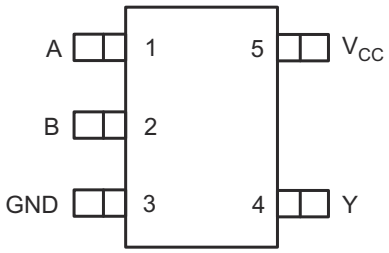


图 6-1. DCK or DBV Package, 5-Pin SC70 or SOT-23 (Top View)

表 6-1. Pin Functions

PIN		TYPE(1)	DESCRIPTION
NAME	NO.		
A	1	I	Input A
B	2	I	Input B
GND	3	G	Ground
Y	4	O	Output Y
V_{CC}	5	P	Positive supply

(1) I = Input, O = Output, I/O = Input or Output, G = Ground, P = Power.

7 Specifications

7.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)(1)

			MIN	MAX	UNIT
V_{CC}	Supply voltage range		–0.5	7.0	V
V_I	Input voltage range(2)		–0.5	7.0	V
V_O	Voltage range applied to any output in the high-impedance or power-off state(2)		–0.5	4.6	V
	Voltage range applied to any output in the high or low state(2)		–0.5	V_{CC} + 0.5	V
I_{IK}	Input clamp current	V_I < 0		–20	mA
I_{OK}	Output clamp current	V_O < 0 or V_O > V_{CC}		±20	mA
I_O	Continuous output current			±25	mA
	Continuous current through V_{CC} or GND			±50	mA
T_J	Junction temperature			150	°C
T_{stg}	Storage temperature		–65	150	°C

(1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions* is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
(2) The input negative-voltage and output voltage ratings may be exceeded if the input and output current ratings are observed.

7.2 ESD Ratings

			VALUE	UNIT
$V_{(ESD)}$	Electrostatic discharge	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001(1)	±2000	V
		Machine Model (MM), per JEDEC specification	±200	
		Charged-device model (CDM), per ANSI/ESDA/JEDEC JS-002(2)	±1000	

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

7.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted) (1)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		1.6	5.5	V
V_I	Input voltage		0	5.5	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 1.8 V		–3	mA
		V_{CC} = 2.5 V		–5	
		V_{CC} = 3.3 V		–7	
		V_{CC} = 5.0 V		–8	
I_{OL}	Low-level output current	V_{CC} = 1.8 V		3	mA
		V_{CC} = 2.5 V		5	
		V_{CC} = 3.3 V		7	
		V_{CC} = 5.0 V		8	
$\Delta t/\Delta v$	Input transition rise or fall rate	V_{CC} = 1.8 V		20	ns/V
		V_{CC} = 3.3 V or 2.5 V		20	
		V_{CC} = 5.0 V		20	

over operating free-air temperature range (unless otherwise noted) (1)

		MIN	MAX	UNIT
T_A	Operating free-air temperature	–40	125	°C

(1) All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.

7.4 Thermal Information

THERMAL METRIC(1)		DBV	DCK	UNIT
		5 PINS	5 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	206	252	°C/W

(1) For more information about traditional and new thermal metrics, see the *IC Package Thermal Metrics* application report, SPRA953.

7.5 Electrical Characteristics

over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS	V_{CC}	T_A = 25°C			T_A = –40°C to 125°C		UNIT
				MIN	TYP	MAX	MIN	MAX	
V_{IH}	High-level input voltage		V_{CC} = 1.65 V to 1.8 V	0.94			1.0		V
			V_{CC} = 2.0 V	1.02			1.03		
			V_{CC} = 2.25 V to 2.5 V	1.135			1.18		
			V_{CC} = 2.75 V	1.21			1.23		
			V_{CC} = 3 V to 3.3 V	1.35			1.37		
			V_{CC} = 3.6 V	1.47			1.48		
			V_{CC} = 4.5 V to 5.0 V	2.02			2.03		
			V_{CC} = 5.5 V	2.1			2.11		
V_{IL}	Low-level input voltage		V_{CC} = 1.65 V to 2.0 V			0.58		0.55	V
			V_{CC} = 2.25 V to 2.75 V			0.75		0.71	
			V_{CC} = 3 V to 3.6 V			0.8		0.65	
			V_{CC} = 4.5 V to 5.5 V			0.8		0.8	
V_{OH}		I_{OH} = –20 µA	1.65 V to 5.5 V	V_{CC} – 0.1			V_{CC} – 0.1		V
		I_{OH} = –2.0 mA	1.65 V	1.28			1.21		
			1.8 V	1.5			1.45		
		I_{OH} = –2.3 mA	2.3 V	2			2		
		I_{OH} = –3 mA		2			1.93		
		I_{OH} = –3 mA	2.5 V	2.25			2.15		
		I_{OH} = –3.0 mA	3.0 V	2.78			2.7		
		I_{OH} = –5.5 mA		2.6			2.49		
		I_{OH} = –5.5 mA	3.3 V	2.9			2.8		
		I_{OH} = –4 mA	4.5 V	4.2			4.1		
		I_{OH} = –8 mA		4.1			3.95		
		I_{OH} = –8 mA	5.0 V	4.6			4.5		
V_{OL}		I_{OL} = 20 µA	1.65 V to 5.5 V			0.1		0.1	V
		I_{OL} = 1.9 mA	1.65 V			0.2		0.25	
		I_{OH} = 2.3 mA	2.3 V			0.1		0.15	
		I_{OH} = 3 mA				0.15		0.2	
		I_{OL} = 3 mA	3.0 V			0.1		0.15	
		I_{OL} = 5.5 mA				0.2		0.252	
		I_{OL} = 4 mA	4.5 V			0.15		0.2	
		I_{OL} = 8 mA				0.3		0.35	
I_I	A input	V_I = 0 V or V_{CC}	0 V, 1.8 V, 2.5 V, 3.3 V, 5.5 V			0.12		±1	µA

over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	V_{CC}	T_A = 25°C			T_A = –40°C to 125°C		UNIT
			MIN	TYP	MAX	MIN	MAX	
I_{CC}	V_I = 0 V or V_{CC}, I_O = 0; open on loading	5.0 V			1		10	μA
		3.3 V			1		10	
		2.5 V			1		10	
		1.8 V			1		10	
ΔI_{CC}	One input at 0.3 V or 3.4 V, Other inputs at 0 or V_{CC}, I_O = 0	5.5 V			1.35		1.5	mA
	One input at 0.3 V or 1.1 V Other inputs at 0 or V_{CC}, I_O = 0	1.8 V			10		10	μA
C_i	V_I = V_{CC} or GND	3.3 V		2	10	2	10	pF
C_o	V_O = V_{CC} or GND	3.3 V		2.5		2.5		pF

7.6 Switching Characteristics

over recommended operating free-air temperature range (unless otherwise noted) (see Parameter Measurement Information)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	FREQUENCY (TYP)	V_{CC}	C_L	T_A = 25°C			T_A = –65°C to 125°C			UNIT
						MIN	TYP	MAX	MIN	TYP	MAX	
t_{pd}	Any In	Y	DC to 50 MHz	5.0 V	15 pF		4	5		4	5	ns
					30 pF		5.5	7.0		5.5	7.0	
				3.3 V	15 pF		4.8	5		5	5.5	ns
					30 pF		5	5.5		5.5	6.5	
			DC to 25 MHz	2.5 V	15 pF		6	6.5		7	7.5	ns
					30 pF		6.5	7.5		7.5	8.5	
			DC to 15 MHz	1.8 V	15 pF		10.5	11		11	12	ns
					30 pF		12	13		12	14	

7.7 Operating Characteristics

T_A = 25°C

PARAMETER		TEST CONDITIONS	V_{CC}	TYP	UNIT
C_{pd}	Power dissipation capacitance	f = 1 MHz and 10 MHz	1.8 V ± 0.15 V	10	pF
			2.5 V ± 0.2 V	10	
			3.3 V ± 0.3 V	10	
			5.5 V ± 0.5 V	10	

7.8 Typical Characteristics

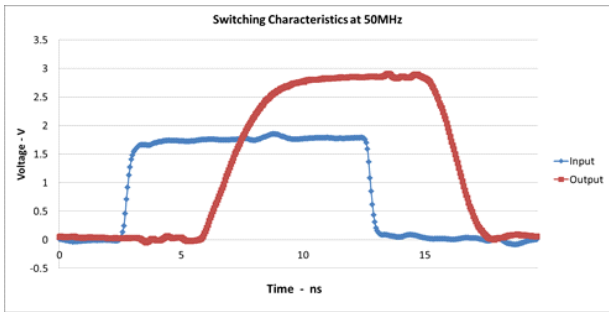


图 7-1. Excellent Signal Integrity (1.8 V to 3.3 V at 3.3-V V_{CC})

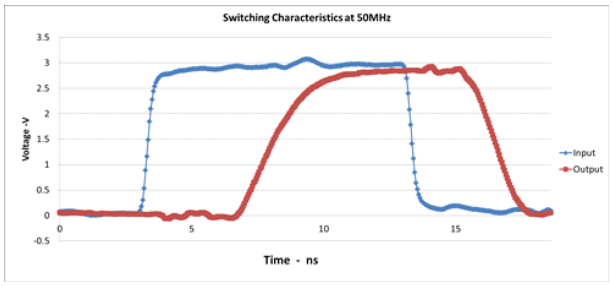


图 7-2. Excellent Signal Integrity (3.3 V to 3.3 V at 3.3-V V_{CC})

7.8 Typical Characteristics (continued)

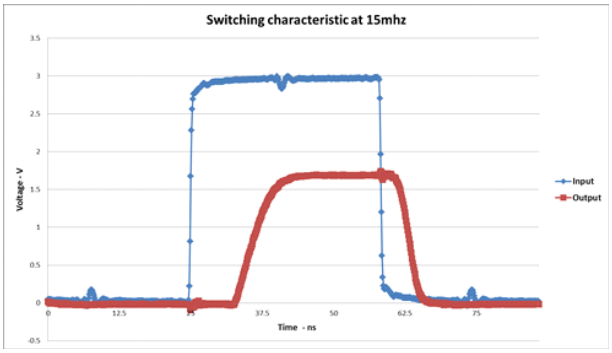


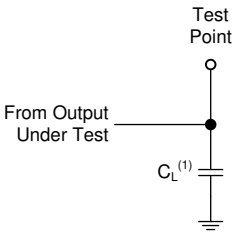
图 7-3. Excellent Signal Integrity (3.3 V to 1.8 V at 1.8-V V_{CC})

8 Parameter Measurement Information

Phase relationships between waveforms were chosen arbitrarily. All input pulses are supplied by generators having the following characteristics: PRR ≤ 1 MHz, Z_O = 50 Ω.

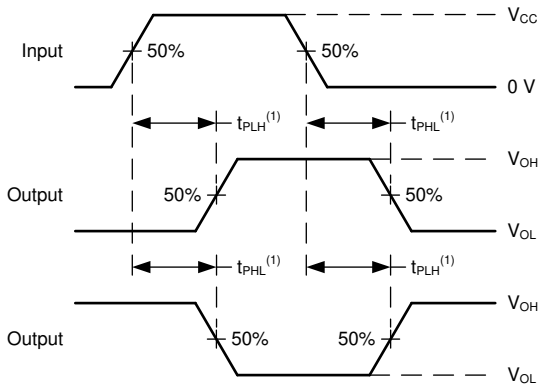
For clock inputs, f_{max} is measured when the input duty cycle is 50%.

The outputs are measured one at a time with one input transition per measurement.



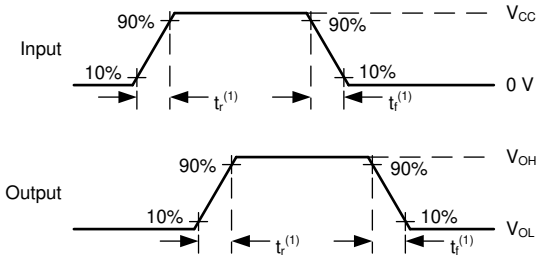
(1) C_L includes probe and test-fixture capacitance.

图 8-1. Load Circuit for Push-Pull Outputs



(1) The greater between t_{PLH} and t_{PHL} is the same as t_{pd}.

图 8-2. Voltage Waveforms Propagation Delays



(1) The greater between t_r and t_f is the same as t_t.

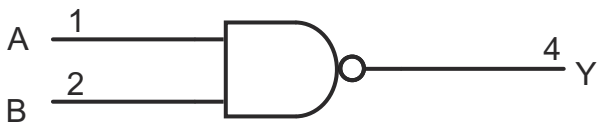
图 8-3. Voltage Waveforms, Input and Output Transition Times

9 Detailed Description

9.1 Overview

The SN74LV1T00 contains one independent dual input NAND gate with extended voltage operation to allow for level translation. Each gate performs the Boolean function $Y = \overline{A \bullet B}$ in positive logic. The output level is referenced to the supply voltage (V_{CC}) and supports 1.8-V, 2.5-V, 3.3-V, and 5-V CMOS levels.

9.2 Functional Block Diagram



9.3 Feature Description

9.3.1 Clamp Diode Structure

The outputs to this device have both positive and negative clamping diodes, and the inputs to this device have negative clamping diodes only as depicted in 图 9-1.

CAUTION

Voltages beyond the values specified in the *Absolute Maximum Ratings* table can cause damage to the device. The input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.

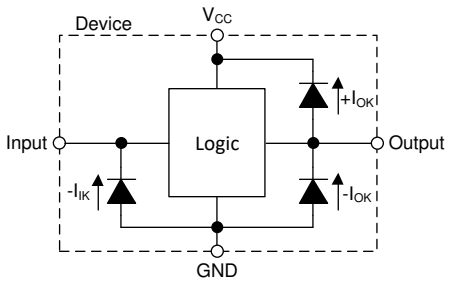


图 9-1. Electrical Placement of Clamping Diodes for Each Input and Output

9.3.2 Balanced CMOS Push-Pull Outputs

This device includes balanced CMOS push-pull outputs. The term *balanced* indicates that the device can sink and source similar currents. The drive capability of this device may create fast edges into light loads so routing and load conditions should be considered to prevent ringing. Additionally, the outputs of this device are capable of driving larger currents than the device can sustain without being damaged. It is important for the output power of the device to be limited to avoid damage due to overcurrent. The electrical and thermal limits defined in the *Absolute Maximum Ratings* must be followed at all times.

Unused push-pull CMOS outputs should be left disconnected.

9.3.3 LVxT Enhanced Input Voltage

The SN74LV1T00 belongs to TI's LVxT family of Logic devices with integrated voltage level translation. This family of devices was designed with reduced input voltage thresholds to support up-translation, and inputs tolerant of signals with up to 5.5 V levels to support down-translation. The output voltage will always be referenced to the supply voltage (V_{CC}), as described in the *Electrical Characteristics* table. To ensure proper functionality, input signals must remain at or below the specified $V_{IH(MIN)}$ level for a HIGH input state, and at or below the specified $V_{IL(MAX)}$ for a LOW input state. 图 9-2 shows the typical V_{IH} and V_{IL} levels for the LVxT family of devices, as well as the voltage levels for standard CMOS devices for comparison.

The inputs are high impedance and are typically modeled as a resistor in parallel with the input capacitance given in the *Electrical Characteristics*. The worst case resistance is calculated with the maximum input voltage, given in the *Absolute Maximum Ratings*, and the maximum input leakage current, given in the *Electrical Characteristics*, using Ohm's law (R = V ÷ I).

The inputs require that input signals transition between valid logic states quickly, as defined by the input transition time or rate in the *Recommended Operating Conditions* table. Failing to meet this specification will result in excessive power consumption and could cause oscillations. More details can be found in the *Implications of Slow or Floating CMOS Inputs* application report.

Do not leave inputs floating at any time during operation. Unused inputs must be terminated at V_{CC} or GND. If a system will not be actively driving an input at all times, a pull-up or pull-down resistor can be added to provide a valid input voltage during these times. The resistor value will depend on multiple factors; however, a 10-kΩ resistor is recommended and will typically meet all requirements.

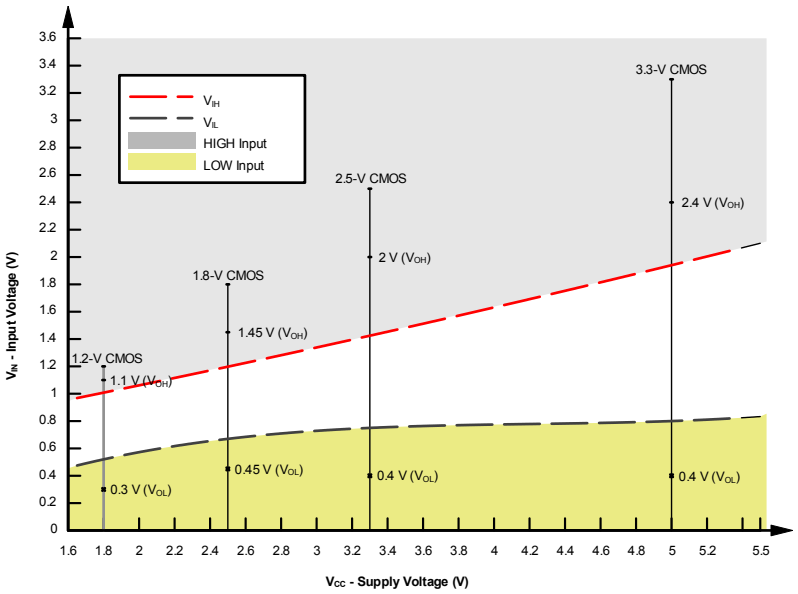


图 9-2. LVxT Input Voltage Levels

9.3.3.1 Down Translation

Signals can be translated down using the SN74LV1T00. The voltage applied at the V_{CC} will determine the output voltage and the input thresholds as described in the *Recommended Operating Conditions* and *Electrical Characteristics* tables.

When connected to a high-impedance input, the output voltage will be approximately V_{CC} in the HIGH state, and 0 V in the LOW state. Ensure that the input signals in the HIGH state are between $V_{IH(MIN)}$ and 5.5 V, and input signals in the LOW state are lower than $V_{IL(MAX)}$ as shown in 图 9-2.

For example, standard CMOS inputs for devices operating at 5.0 V, 3.3 V or 2.5 V can be down-translated to match 1.8 V CMOS signals when operating from 1.8-V V_{CC}. See 图 9-3.

Down Translation Combinations:

- 1.8-V V_{CC} – Inputs from 2.5 V, 3.3 V, and 5.0 V
- 2.5-V V_{CC} – Inputs from 3.3 V and 5.0 V
- 3.3-V V_{CC} – Inputs from 5.0 V

9.3.3.2 Up Translation

Input signals can be up translated using the SN74LV1T00. The voltage applied at V_{CC} will determine the output voltage and the input thresholds as described in the *Recommended Operating Conditions* and *Electrical Characteristics* tables. When connected to a high-impedance input, the output voltage will be approximately V_{CC} in the HIGH state, and 0 V in the LOW state.

The inputs have reduced thresholds that allow for input high-state levels which are much lower than standard values. For example, standard CMOS inputs for a device operating at a 5-V supply will have a $V_{IH(MIN)}$ of 3.5 V. For the SN74LV1T00, $V_{IH(MIN)}$ with a 5-V supply is only 2 V, which would alow for up-translation from a typical 2.5-V to 5-V signals.

Ensure that the input signals in the HIGH state are above $V_{IH(MIN)}$ and input signals in the LOW state are lower than $V_{IL(MAX)}$ as shown in 图 9-3.

Up Translation Combinations:

- 1.8-V V_{CC} – Inputs from 1.2 V
- 2.5-V V_{CC} – Inputs from 1.8 V
- 3.3-V V_{CC} – Inputs from 1.8 V and 2.5 V
- 5.0-V V_{CC} – Inputs from 2.5 V and 3.3 V

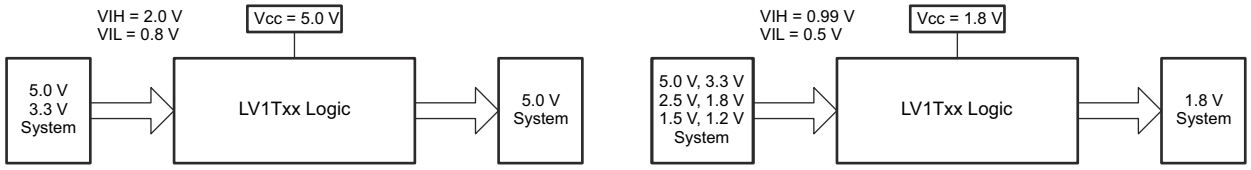


图 9-3. LVxT Up and Down Translation Example

9.4 Device Functional Modes

Function Table lists the functional modes of the SN74LV1T00.

表 9-1. Function Table

INPUTS(1) (Lower Level Input)		OUTPUT (V_{CC} CMOS)(2)
A	**B**	**Y**
H	H	L
L	X	H
X	L	H
SUPPLY V_{CC} = 3.3V		
A	B	Y
V_{IH}(min) =1.35 V		V_{OH}(min) = 2.9 V
V_{IL}(max) =0.8 V		V_{OL}(max)= 0.2 V

(1) H = High Voltage Level, L = Low Voltage Level, X = Do not Care, Z = High Impedance
(2) H = Driving High, L = Driving Low, Z = High Impedance State

10 Power Supply Recommendations

The power supply can be any voltage between the minimum and maximum supply voltage rating located in the *Recommended Operating Conditions*. Each V_{CC} terminal should have a good bypass capacitor to prevent power disturbance. A 0.1-μF capacitor is recommended for this device. It is acceptable to parallel multiple bypass caps to reject different frequencies of noise. The 0.1-μF and 1-μF capacitors are commonly used in parallel. The bypass capacitor should be installed as close to the power terminal as possible for best results, as shown in the following layout example.

11 Layout

11.1 Layout Guidelines

When using multiple-input and multiple-channel logic devices inputs must not ever be left floating. In many cases, functions or parts of functions of digital logic devices are unused; for example, when only two inputs of a triple-input AND gate are used or only 3 of the 4 buffer gates are used. Such unused input pins must not be left unconnected because the undefined voltages at the outside connections result in undefined operational states. All unused inputs of digital logic devices must be connected to a logic high or logic low voltage, as defined by the input voltage specifications, to prevent them from floating. The logic level that must be applied to any particular unused input depends on the function of the device. Generally, the inputs are tied to GND or V_{CC}, whichever makes more sense for the logic function or is more convenient.

12 Device and Documentation Support

12.1 接收文档更新通知

要接收文档更新通知，请导航至 ti.com 上的器件产品文件夹。点击 *订阅更新* 进行注册，即可每周接收产品信息更改摘要。有关更改的详细信息，请查看任何已修订文档中包含的修订历史记录。

12.2 支持资源

TI E2E™ 支持论坛是工程师的重要参考资料，可直接从专家获得快速、经过验证的解答和设计帮助。搜索现有解答或提出自己的问题可获得所需的快速设计帮助。

链接的内容由各个贡献者“按原样”提供。这些内容并不构成 TI 技术规范，并且不一定反映 TI 的观点；请参阅 TI 的《使用条款》。

12.3 Trademarks

TI E2E™ is a trademark of Texas Instruments.
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12.4 Electrostatic Discharge Caution

This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

12.5 术语表

TI 术语表　　本术语表列出并解释了术语、首字母缩略词和定义。

13 Mechanical, Packaging, and Orderable Information

The following packaging information and addendum reflect the most current data available for the designated devices. This data is subject to change without notice and revision of this document.

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
SN74LV1T00DBVR	ACTIVE	SOT-23	DBV	5	3000	RoHS & Green	NIPDAU | SN	Level-1-260C-UNLIM	-40 to 125	(NEA3, NEAJ, NEAS)	Samples
SN74LV1T00DBVRG4	ACTIVE	SOT-23	DBV	5	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	NEA3	Samples
SN74LV1T00DCKR	ACTIVE	SC70	DCK	5	3000	RoHS & Green	NIPDAU | SN	Level-1-260C-UNLIM	-40 to 125	(WA3, WAJ, WAS)	Samples
SN74LV1T00DCKRG4	ACTIVE	SC70	DCK	5	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM		WA3	Samples

(1) The marketing status values are defined as follows:
ACTIVE: Product device recommended for new designs.
LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.
NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.
PREVIEW: Device has been announced but is not in production. Samples may or may not be available.
OBSOLETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".
RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.
Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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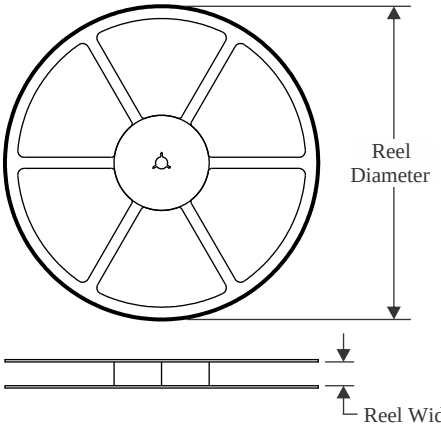
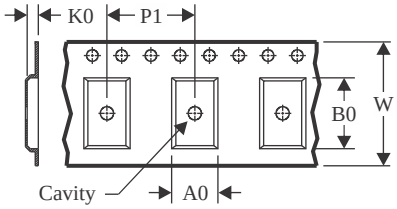
In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

TAPE AND REEL INFORMATION

REEL DIMENSIONS

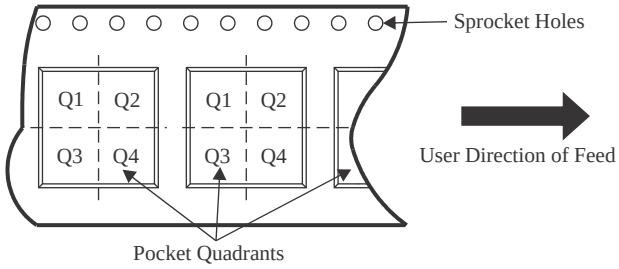


TAPE DIMENSIONS



A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

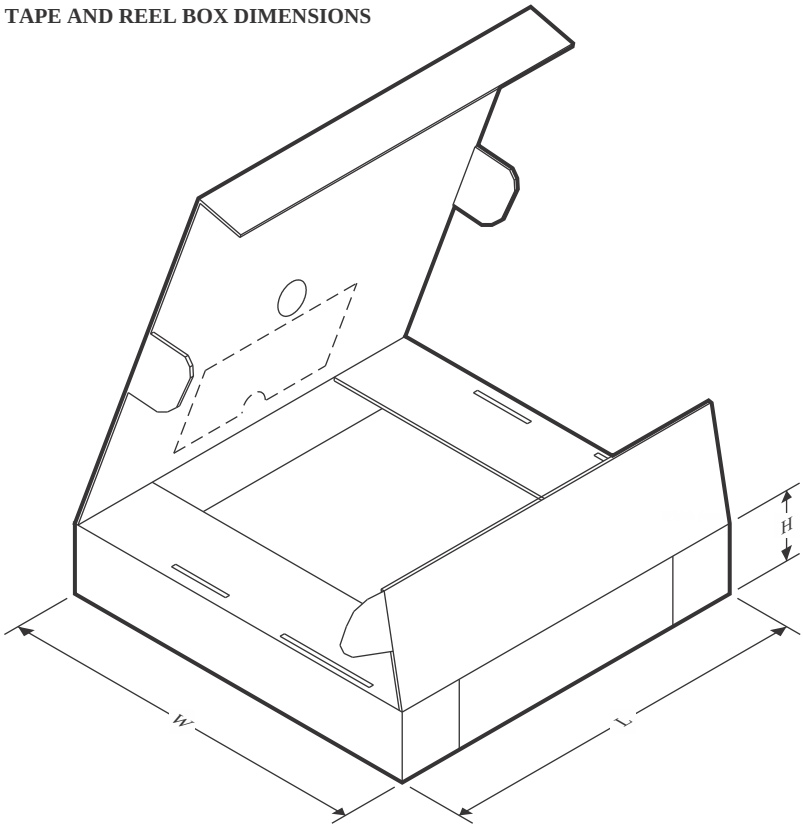
QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN74LV1T00DBVR	SOT-23	DBV	5	3000	180.0	8.4	3.23	3.17	1.37	4.0	8.0	Q3
SN74LV1T00DBVR	SOT-23	DBV	5	3000	178.0	9.0	3.3	3.2	1.4	4.0	8.0	Q3
SN74LV1T00DBVRG4	SOT-23	DBV	5	3000	178.0	9.2	3.3	3.23	1.55	4.0	8.0	Q3
SN74LV1T00DCKR	SC70	DCK	5	3000	178.0	9.2	2.4	2.4	1.22	4.0	8.0	Q3
SN74LV1T00DCKR	SC70	DCK	5	3000	178.0	9.0	2.4	2.5	1.2	4.0	8.0	Q3
SN74LV1T00DCKRG4	SC70	DCK	5	3000	178.0	9.2	2.4	2.4	1.22	4.0	8.0	Q3

TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

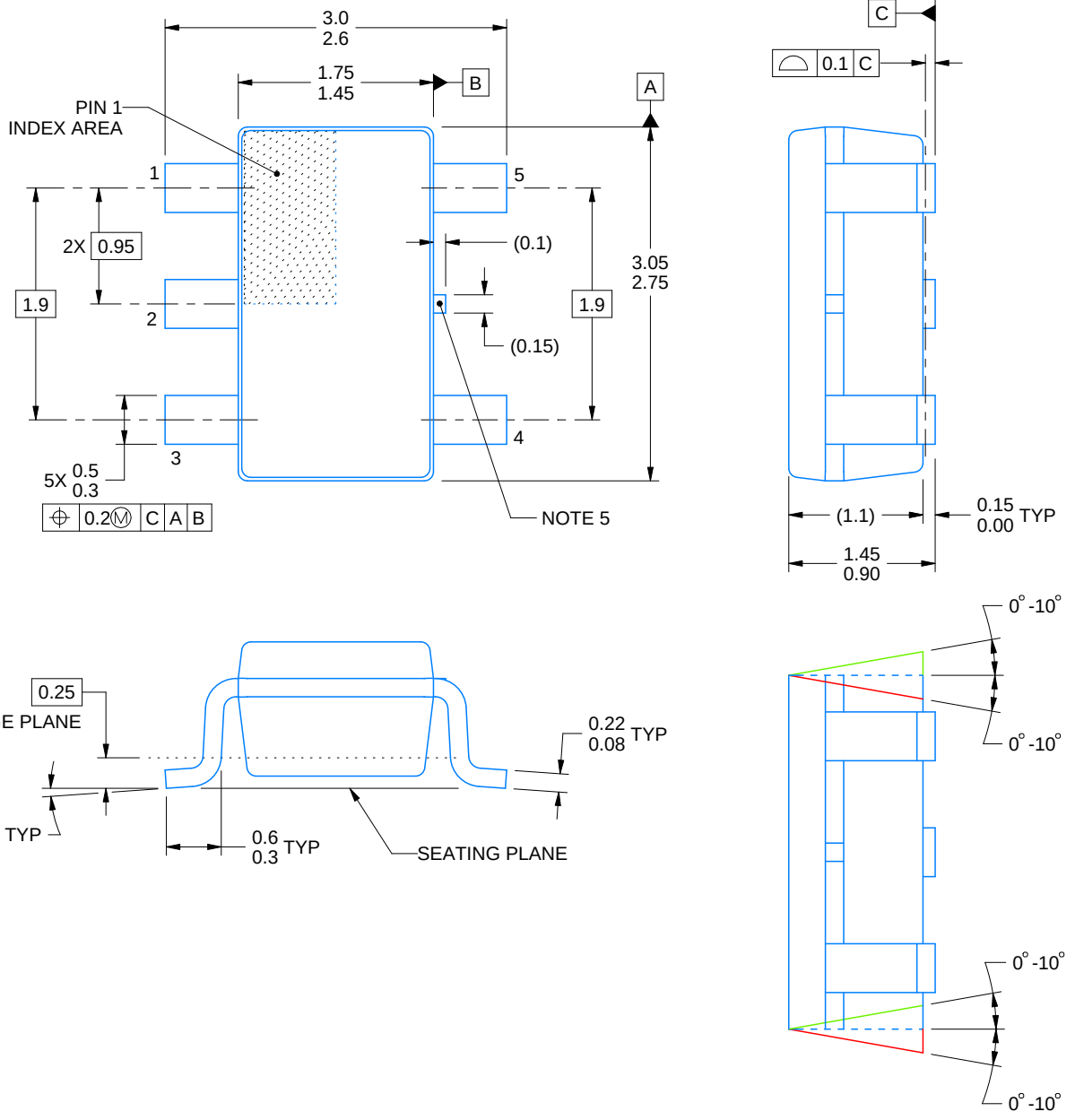
Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN74LV1T00DBVR	SOT-23	DBV	5	3000	202.0	201.0	28.0
SN74LV1T00DBVR	SOT-23	DBV	5	3000	180.0	180.0	18.0
SN74LV1T00DBVRG4	SOT-23	DBV	5	3000	180.0	180.0	18.0
SN74LV1T00DCKR	SC70	DCK	5	3000	180.0	180.0	18.0
SN74LV1T00DCKR	SC70	DCK	5	3000	180.0	180.0	18.0
SN74LV1T00DCKRG4	SC70	DCK	5	3000	180.0	180.0	18.0

PACKAGE OUTLINE

DBV0005A

SOT-23 - 1.45 mm max height

SMALL OUTLINE TRANSISTOR

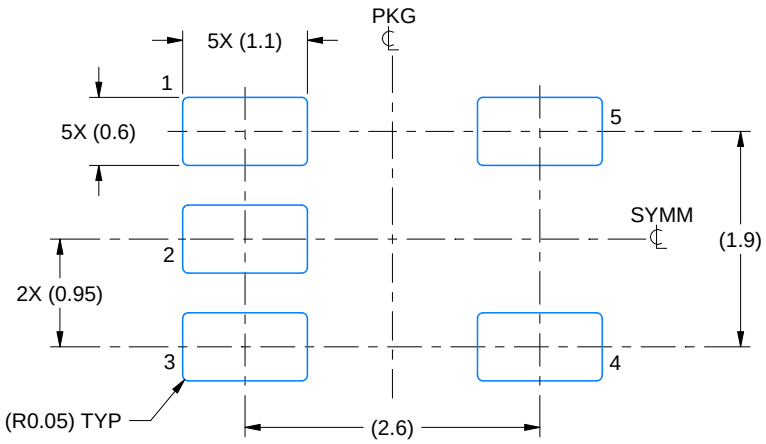


ALTERNATIVE PACKAGE SINGULATION VIEW

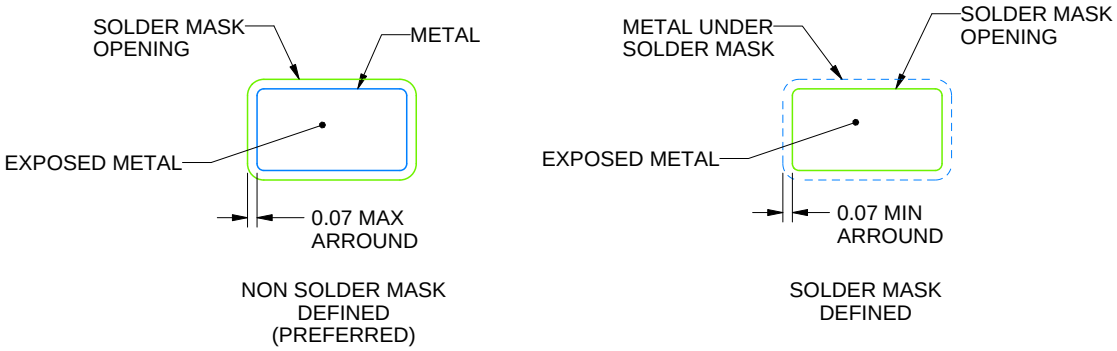
4214839/H 09/2023

NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. Refernce JEDEC MO-178.
4. Body dimensions do not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.25 mm per side.
5. Support pin may differ or may not be present.



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE:15X

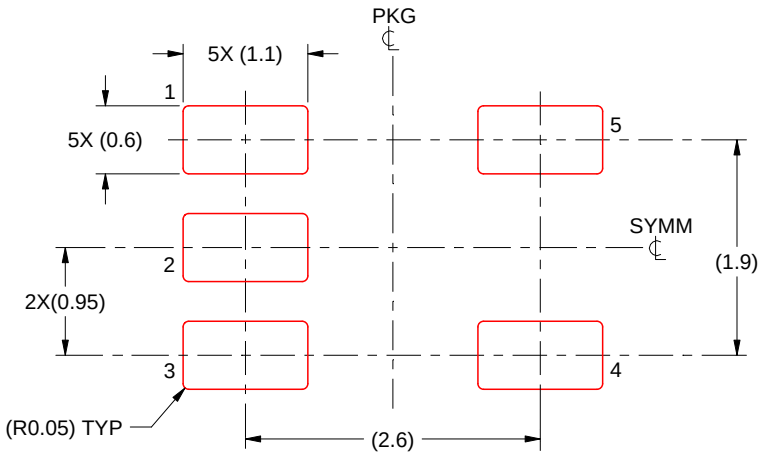


SOLDER MASK DETAILS

4214839/H 09/2023

NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE:15X

4214839/H 09/2023

NOTES: (continued)

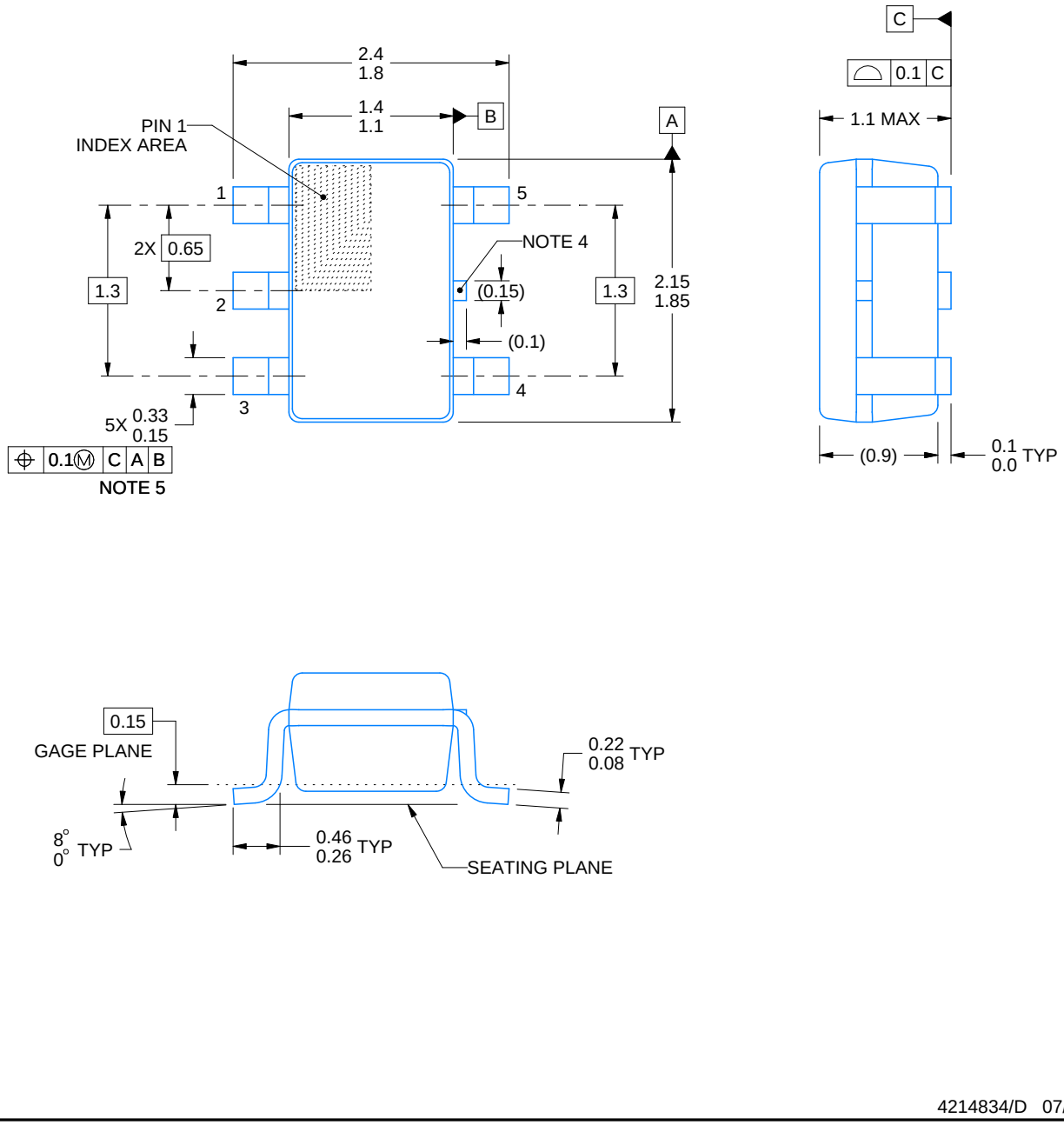
8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

PACKAGE OUTLINE

DCK0005A

SOT - 1.1 max height

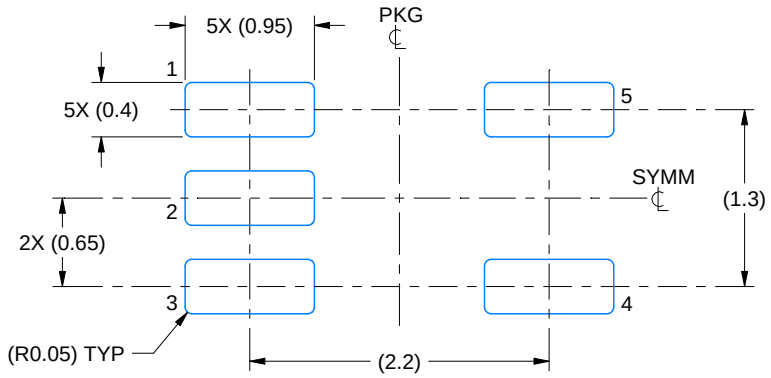
SMALL OUTLINE TRANSISTOR



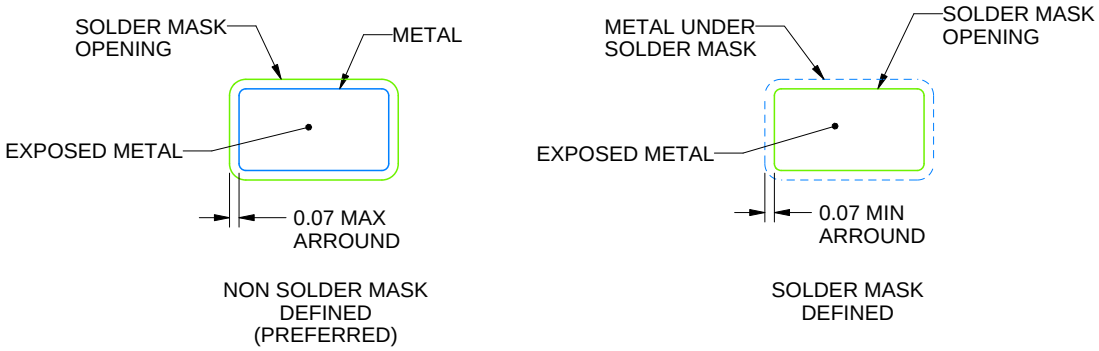
4214834/D 07/2023

NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. Refernce JEDEC MO-203.
4. Support pin may differ or may not be present.
5. Lead width does not comply with JEDEC.



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE:18X

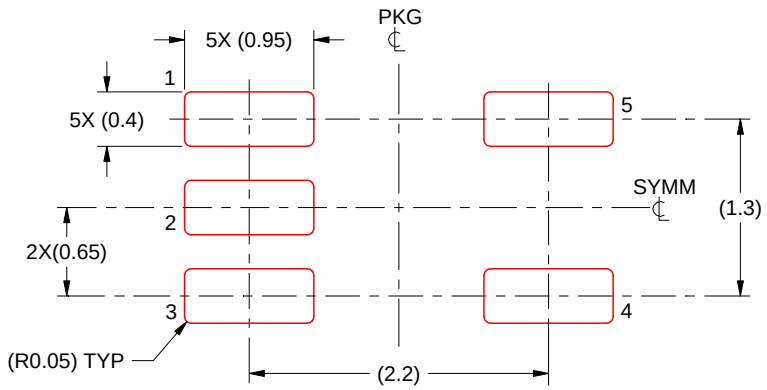


SOLDER MASK DETAILS

4214834/D 07/2023

NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SOLDER PASTE EXAMPLE
BASED ON 0.125 THICK STENCIL
SCALE:18X

4214834/D 07/2023

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

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